

N-Channel 600V (D-S) Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	2.2
Q_g (Max.) (nC)	39	
Q_{gs} (nC)	10	
Q_{gd} (nC)	19	
Configuration	Single	

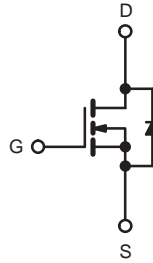
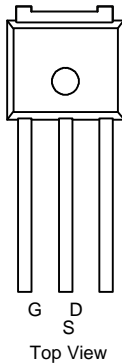
FEATURES

- Ultra Low Gate Charge
- Reduced Gate Drive Requirement
- Enhanced 30 V, V_{GS} Rating
- Reduced C_{iss} , C_{oss} , C_{rss}
- Extremely High Frequency Operation
- Repetitive Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
 COMPLIANT

TO-251



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	4	A
		$T_C = 100\text{ }^{\circ}\text{C}$		2.9	
Pulsed Drain Current ^a			I_{DM}	25	
Linear Derating Factor				1.0	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b			E_{AS}	530	mJ
Repetitive Avalanche Current ^a			I_{AR}	6.2	A
Repetitive Avalanche Energy ^a			E_{AR}	13	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		P_D	125	W
Peak Diode Recovery dV/dt ^c			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s			300 ^d	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 25\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 6.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 6.2\text{ A}$, $dI/dt \leq 80\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

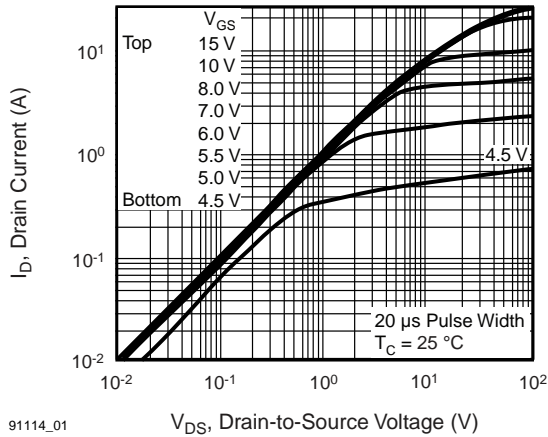
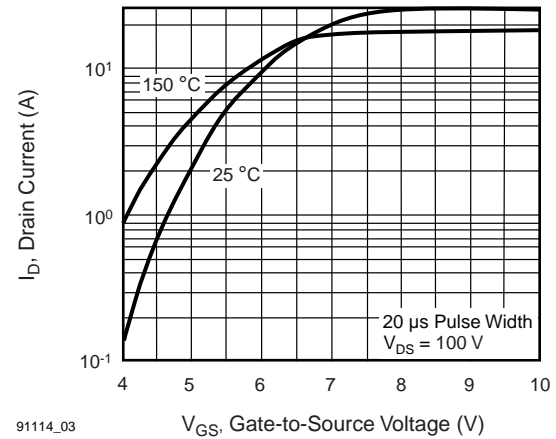
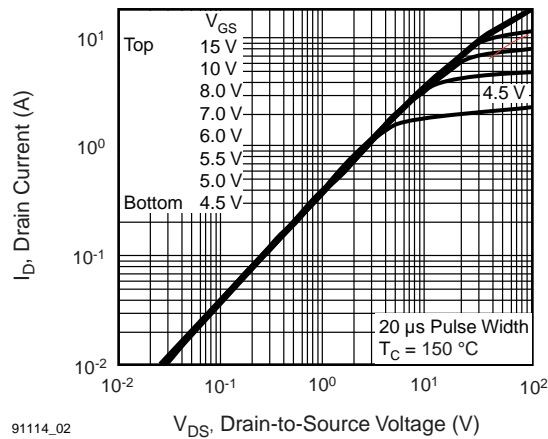
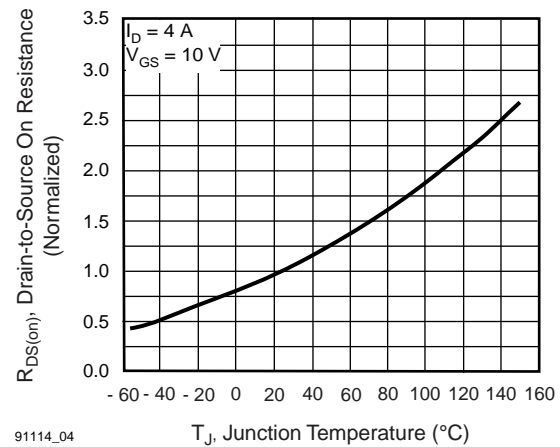
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

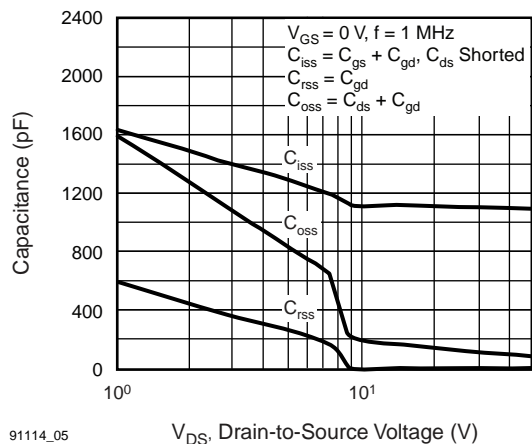
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.70	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V		-	-	100	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C		-	-	500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.7 A ^b	-	2.2	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = 100 V, I _D = 3.7 A ^b		3.7	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V V _{DS} = 25 V f = 1.0 MHz, see fig. 5		-	1100	-	pF
Output Capacitance	C _{oss}			-	140	-	
Reverse Transfer Capacitance	C _{rss}			-	15	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 4 A, V _{DS} = 360 V, see fig. 6 and 13 ^b	-	-	39	nC
Gate-Source Charge	Q _{gs}			-	-	10	
Gate-Drain Charge	Q _{gd}			-	-	19	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 4 A R _g = 9.1 Ω, R _D = 47 Ω, see fig. 10 ^b		-	12	-	ns
Rise Time	t _r			-	20	-	
Turn-Off Delay Time	t _{d(off)}			-	27	-	
Fall Time	t _f			-	17	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	4.0	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	25	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 4 A, V _{GS} = 0 V ^b		-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 4 A, dI/dt = 100 A/μs ^b		-	440	680	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	2.1	3.2	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

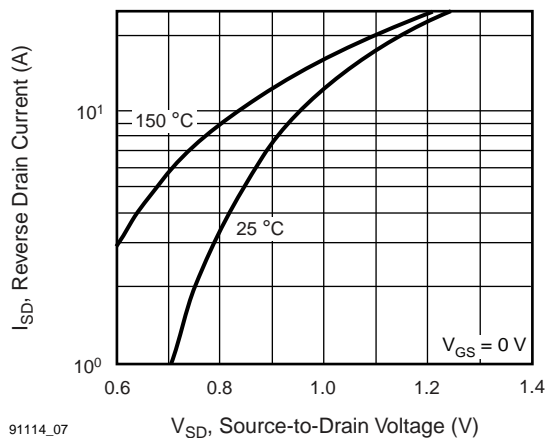
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^{\circ}\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature



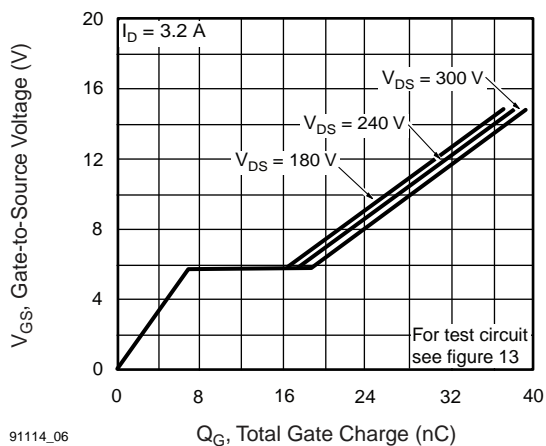
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



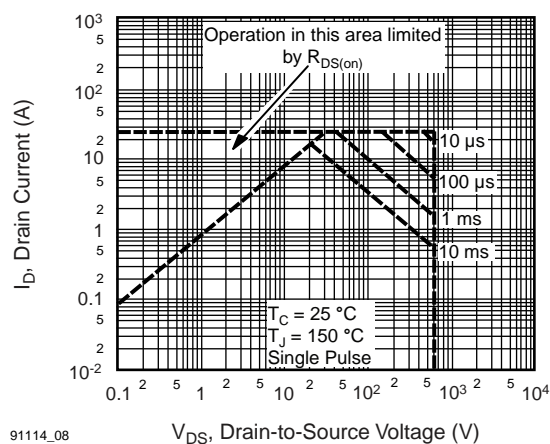
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



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Fig. 8 - Maximum Safe Operating Area

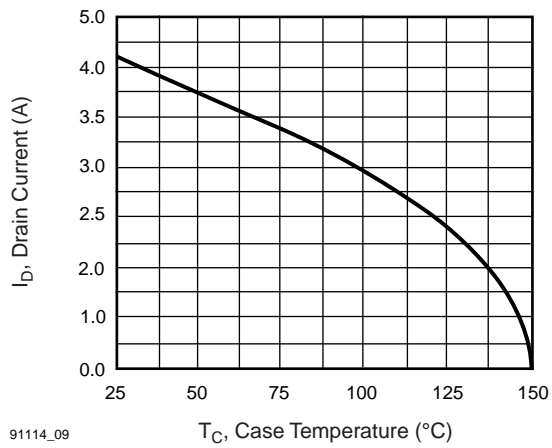


Fig. 9 - Maximum Drain Current vs. Case Temperature

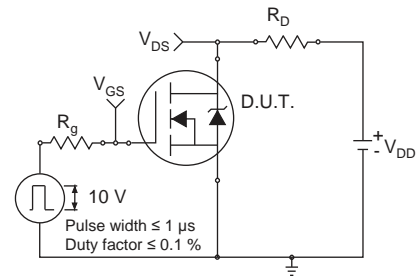


Fig. 10a - Switching Time Test Circuit

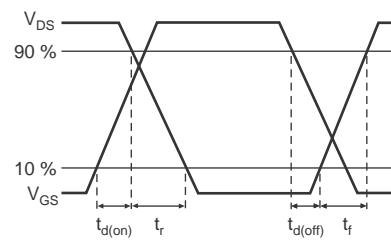


Fig. 10b - Switching Time Waveforms

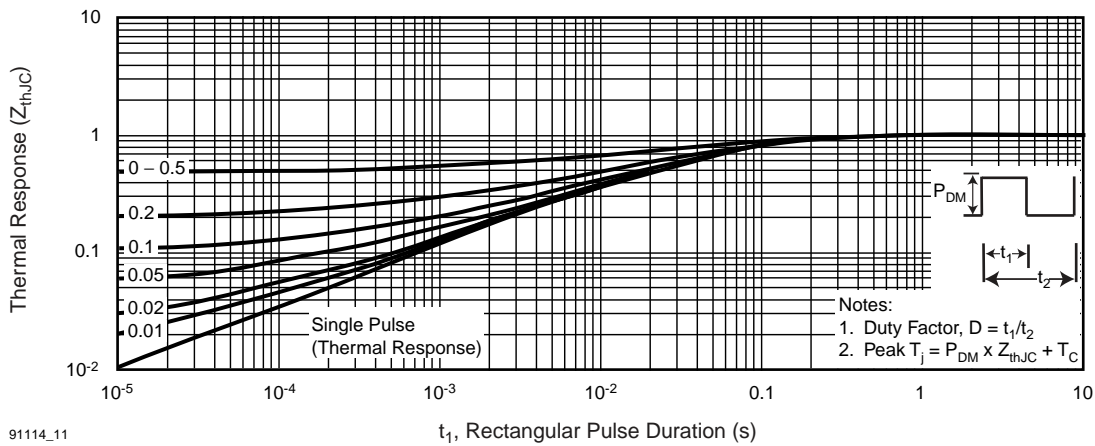


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

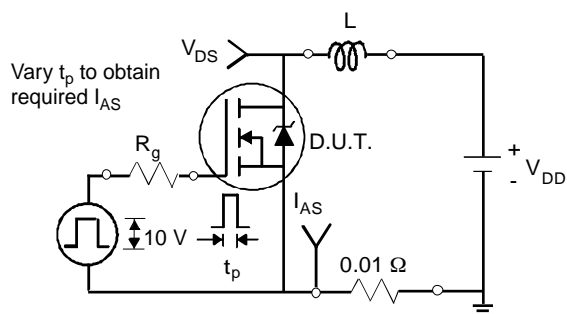


Fig. 12a - Unclamped Inductive Test Circuit

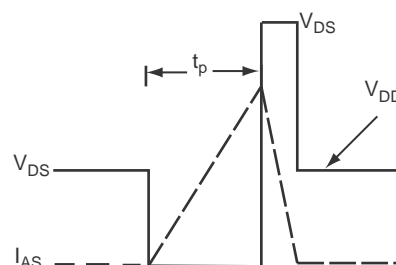


Fig. 12b - Unclamped Inductive Waveforms

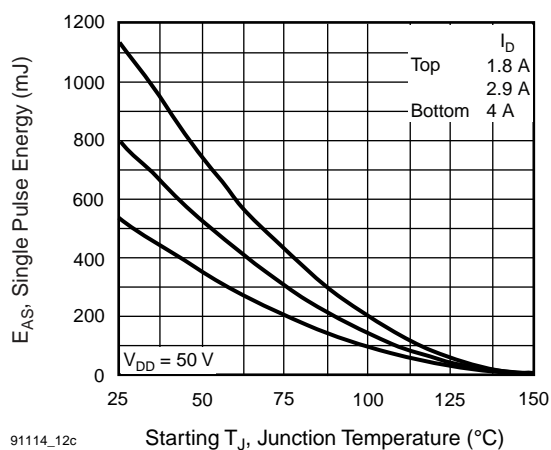


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

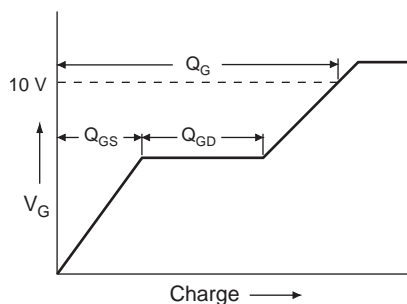


Fig. 13a - Basic Gate Charge Waveform

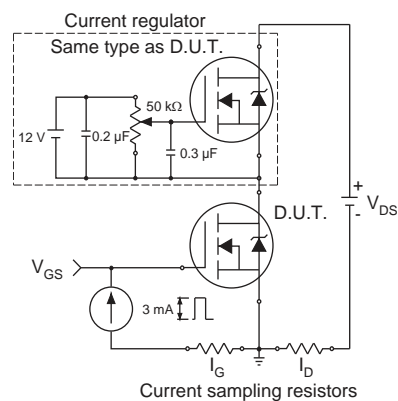
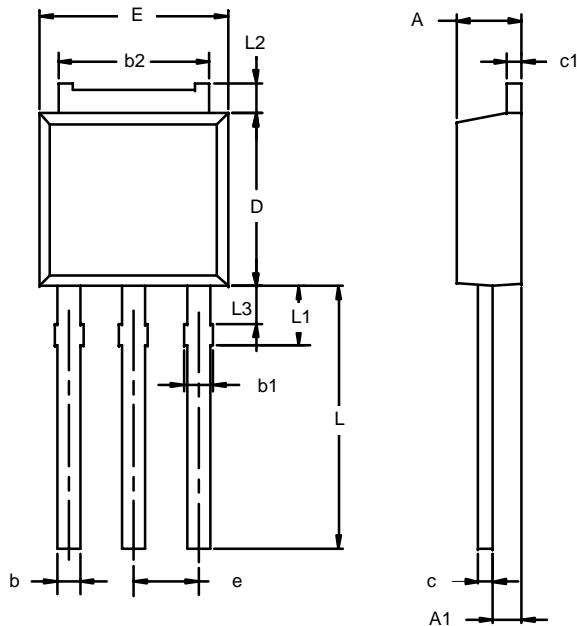


Fig. 13b - Gate Charge Test Circuit

TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	8.89	9.53	0.350	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346				

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